

DESCRIPTION:

The products are gate driver opto-couplers in the SOP5 package. The device consists of an infrared LED optically coupled to an integrated high-gain, high-speed photodetector IC chip. It provides guaranteed performance and specifications at temperature up to 110°C. It is physically smaller and compliant with international safety standards for reinforced insulation. It thus provides a smaller footprint solution for applications that require safety standard certification. An internal noise shield provides a guaranteed common-mode transient immunity of ± 35 kV/ μ s. It is ideal for small class IGBT and power MOSFET gate drive. The products are widely used in industrial inverters, IGBT gate drivers, MOSFET gate drivers, induction cooktop and home appliances.



MAIN FEATURES

- 0.1A maximum peak output current
- High isolation 3750 VRMS
- Buffer logic type
- Operating temperature range -40°C to 110°C
- REACH & RoHS compliance
- HBM: H3A; MM: M4; CDM: C3
- CQC approved
- VDE approved
- UL approved

Truth Table

| Input | LED | Output |
|-------|-----|--------|
| H | ON | L |
| L | OFF | H |

ABSOLUTE MAXIMUM RATINGS (Temperature=25°C)

| Parameter | | Symbol | Value | Unit |
|-----------|----------------------|----------|----------------|------|
| LED | Forward Current | I_F | 50 | mA |
| | Peak Forward Current | I_{FP} | 1 ^① | A |
| | Reverse Voltage | V_R | 6 | V |

| | | | | |
|-------------------------|-------------------|-----------|-------------------|------------------|
| | Power Dissipation | P_D | 100 | mW |
| Detector | Output Voltage | V_O | 30 | V |
| | Supply Voltage | V_{CC} | 30 | V |
| | Power Dissipation | P_C | 400 | mW |
| Isolation Voltage | | V_{iso} | 3750 ^② | V _{rms} |
| Operating Temperature | | T_{opr} | -40~110 | °C |
| Junction Temperature | | T_j | 125 | °C |
| Storage Temperature | | T_{stg} | -55~125 | °C |
| Total Power Dissipation | | P_{tot} | 500 | mW |
| Soldering Temperature | | T_{sol} | 260 | °C |

NOTE1: 100μs pulse, 100Hz frequency

NOTE2: AC for 1minute, R.H.=40~60%

ELECTRICAL CHARACTERISTICS (Temperature=25°C)

| Parameter | | Symbol | Condition | Min. | Typ. | Max. | Unit |
|--------------------------|--------------------------------|--------------------------------|----------------------------|--------------|---------------|------|------|
| Input | Forward Voltage | V_F | $I_F=10mA$ | - | 1.35 | 1.6 | V |
| | Reverse Current | I_R | $V_R=6V$ | - | - | 1 | μA |
| | Terminal Capacitance | C_t | $V=0, f=1MHz$ | - | 60 | - | pF |
| Output | Peak High-level Output Current | I_{OPH} | $V_{CC}=5.5V, V_O=GND$ | - | -350 | -150 | mA |
| | | | $V_{CC}=20V, V_O=GND$ | - | -350 | -160 | mA |
| | Peak Low-level Output Current | I_{OPL} | $I_F=5mA, V_{CC}=V_O=5.5V$ | 150 | 270 | - | mA |
| | | | $I_F=5mA, V_{CC}=V_O=20V$ | 160 | 300 | - | mA |
| | High Level Supply Current | I_{CCH} | $V_{CC}=5.5V$ | - | 2.1 | 3 | mA |
| | | | $V_{CC}=30V$ | - | 2.35 | 3 | mA |
| | Low Level Supply Current | I_{CCL} | $I_F=5mA, V_{CC}=5.5V$ | - | 2.1 | 3 | mA |
| | | | $I_F=5mA, V_{CC}=30V$ | - | 2.35 | 3 | mA |
| | High Level Output Voltage | V_{OH} | $I_O=-3.5mA$ | $V_{CC}-0.2$ | $V_{CC}-0.03$ | - | V |
| | | | $I_O=-6.5mA$ | $V_{CC}-0.4$ | $V_{CC}-0.05$ | - | V |
| Low Level Output Voltage | V_{OL} | $I_F=5mA, V_F=0.8V, I_O=3.5mA$ | - | 0.026 | 0.2 | V | |

| | | | | | | | |
|-------------------------|-----------|--|---|-----|-------|-----|----|
| | | | $I_F=5\text{mA}$, $V_F=0.8\text{V}$, $I_O=6.5\text{mA}$ | - | 0.047 | 0.4 | V |
| Threshold Input Current | I_{FLH} | | $V_{CC}=15\text{V}$, $V_O>1\text{V}$ | - | 1.2 | 5 | mA |
| Threshold Input Voltage | V_{FHL} | | $V_{CC}=15\text{V}$, $V_O<1\text{V}$ | 0.8 | - | - | V |
| Supply Voltage | V_{CC} | | - | 4.5 | - | 30 | V |

SWITCHING SPECIFICATION

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|---|--------------------------------|--|----------|------|------|-------------------|
| Propagation Delay Time to High Output Level | $t_{PLH}^{\text{①}}$ | $R_g=47\Omega$, $C_g=3\text{nF}$, $I_F=0\rightarrow 5\text{mA}$, $V_{CC}=30\text{V}$ | 35 | - | 120 | ns |
| Propagation Delay Time to Low Output Level | $t_{PHL}^{\text{①}}$ | $R_g=47\Omega$, $C_g=3\text{nF}$, $I_F=5\rightarrow 0\text{mA}$, $V_{CC}=30\text{V}$ | 35 | - | 120 | |
| Propagation Delay Difference Between Any Two Parts | $t_{PHL} - t_{PLH}^{\text{①}}$ | $R_g=47\Omega$, $C_g=3\text{nF}$, $I_F=0\leftrightarrow 5\text{mA}$, $V_{CC}=30\text{V}$ | - | - | 40 | |
| Output Rise Time (10 to 90%) | $t_r^{\text{①}}$ | $R_g=47\Omega$, $C_g=3\text{nF}$, $I_F=0\rightarrow 5\text{mA}$, $V_{CC}=30\text{V}$ | - | 3 | 30 | |
| Output Fall Time (90 to 10%) | $t_f^{\text{①}}$ | $R_g=47\Omega$, $C_g=3\text{nF}$, $I_F=5\rightarrow 0\text{mA}$, $V_{CC}=30\text{V}$ | - | 3 | 30 | |
| Common Mode Transient Immunity at High Level Output | $ CM_H $ | $I_F=5\text{mA}$ $V_{CC}=30\text{V}$, $T_a=25^\circ\text{C}$, $V_O(\text{min})=26\text{V}$ $V_{CM}=1000\text{Vpp}$ | ± 35 | - | - | kV/ μs |
| Common Mode Transient Immunity at Low Level Output | $ CM_L $ | $I_F=0\text{mA}$ $V_{CC}=30\text{V}$, $T_a=25^\circ\text{C}$, $V_O(\text{max})=1\text{V}$ $V_{CM}=1000\text{Vpp}$ | ± 35 | - | - | kV/ μs |

All Typical values at $T_a=25^\circ\text{C}$

Note1: Input signal ($f=25\text{kHz}$, $\text{duty}=50\%$, $t_r=t_f=5\text{ns}$ or less). C_L is less than 15 pF which includes probe and stray wiring capacitance.

Recommended Operating Conditions^{①②}

| Characteristics | Symbol | Min. | Typ. | Max. | Unit |
|-------------------------|--------------------------|------|------|------|------|
| Input On-state Current | $I_{F(ON)}$ ^③ | 7 | - | 15 | mA |
| Input Off-state Voltage | $V_{F(OFF)}$ | 0 | - | 0.8 | V |
| Supply Voltage | V_{CC} ^④ | 4.5 | - | 30 | V |
| Operating Frequency | f ^⑤ | - | - | 25 | kHz |

Note1: The recommended operating conditions are given as a design guide necessary to obtain the intended performance of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this datasheet should also be considered.

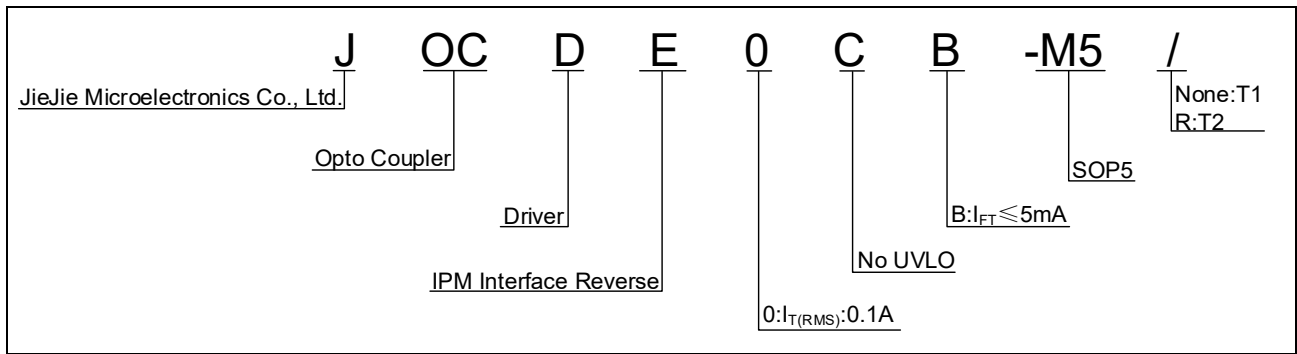
Note2: A ceramic capacitor(0.1 μ F) should be connected between pin 6 (V_{CC}) and pin 4 (GND) to stabilize the operation of a high-gain linear amplifier. Otherwise, this photocoupler may not switch properly. The bypass capacitor should be placed within 1 cm of each pin.

Note3: The rise and fall times of the input on-current should be less than 0.5 μ s.

Note4: If the rising slope of the supply voltage (V_{CC}) for the detector is steep, stable operation of the internal circuits cannot be guaranteed. Be sure to set 3 V/ μ s or less for a rising slope of the V_{CC} .

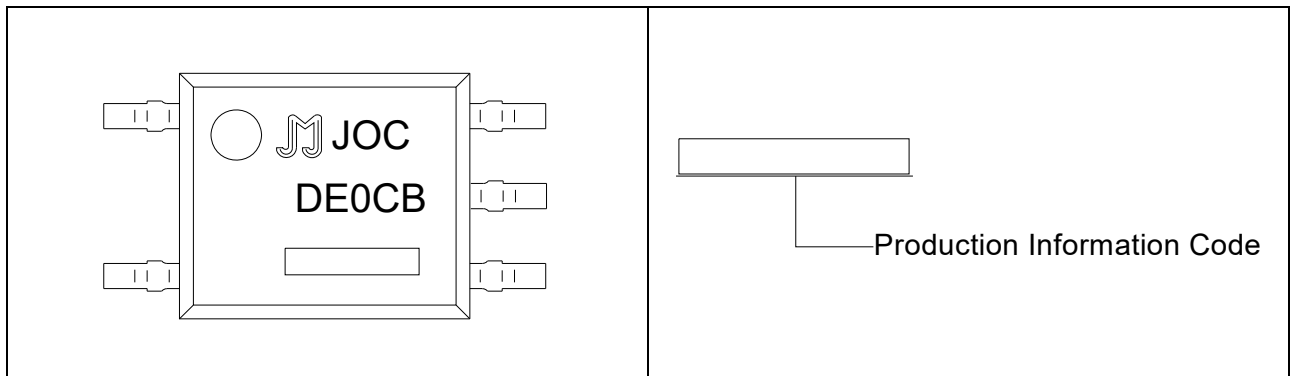
Note5: Denotes the operating range, not the recommended operating condition.

ORDERING INFORMATION



| Packing Quantity | | | |
|------------------|-----------------|----------------------|----------------------------------|
| Option | Quantity | Quantity – Inner box | Quantity –Outer box |
| SOP5 | 3000 Units/Reel | 2 Reels/Inner box | 5 Inner box/Outer box =30k Units |

MARKING



Characteristics Curves

FIG.1: Forward Current vs. Forward Voltage

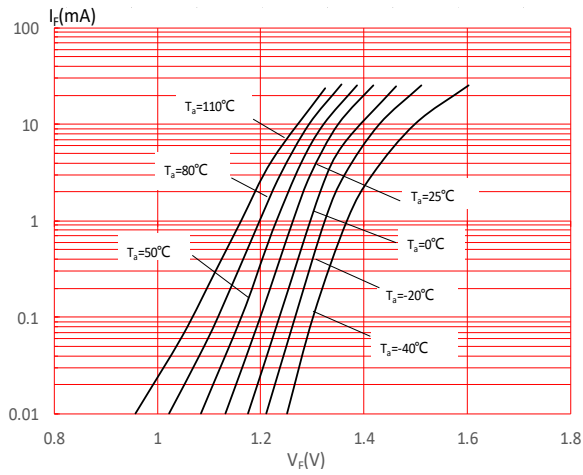


FIG.2: Max. Allowable LED Forward Current vs. Ambient Temperature

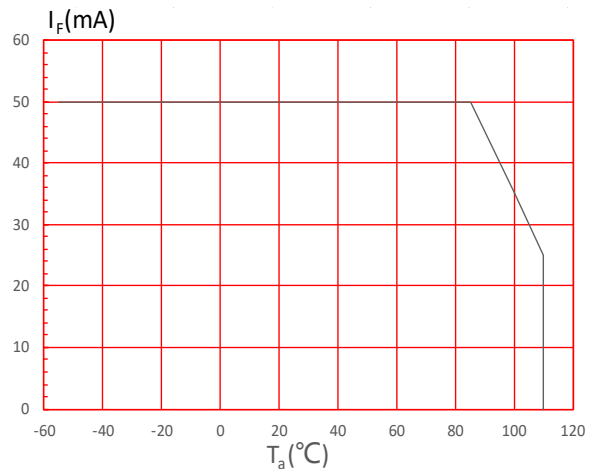


FIG.3: Collector Power Dissipation vs. Ambient Temperature

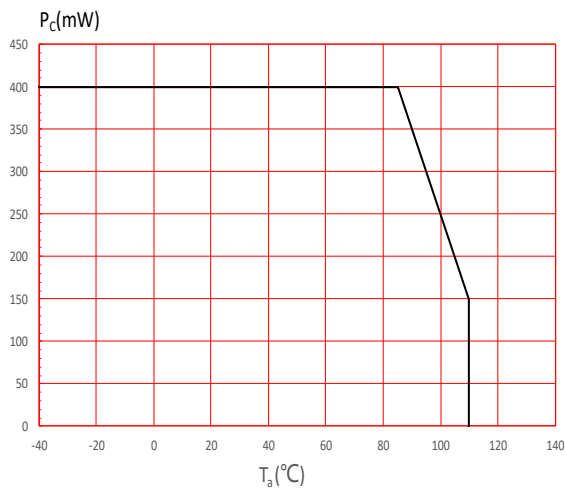


FIG.4: Threshold Input Current vs. Ambient Temperature

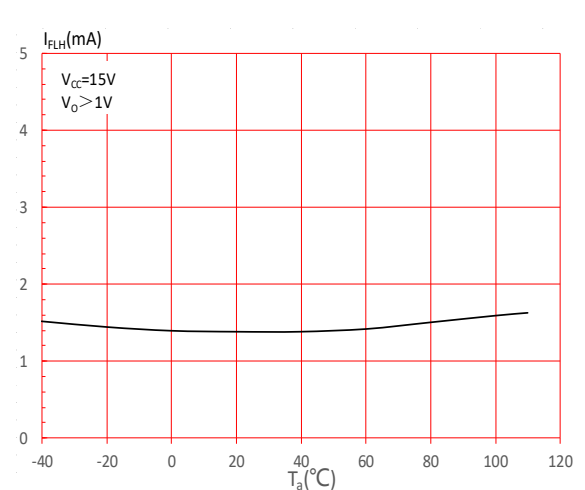


FIG.5: Low-level Supply Current vs. Ambient Temperature

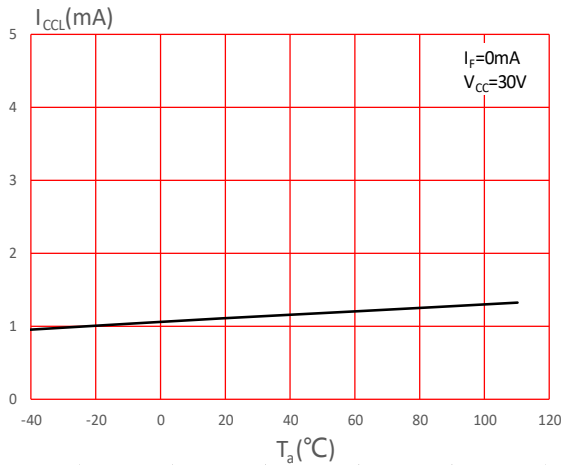


FIG.6: High-level Supply Current vs. Ambient Temperature

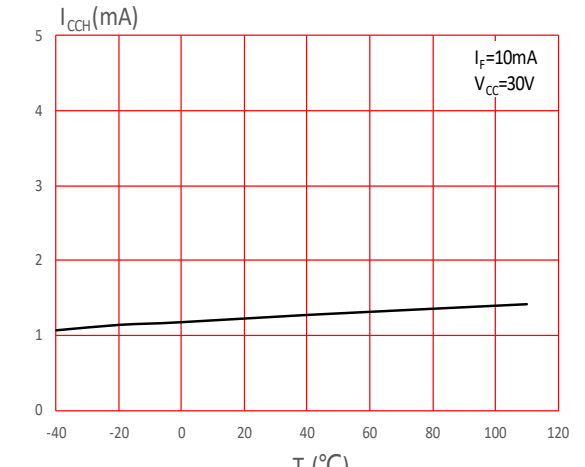


FIG.7: Low-level Output Voltage vs. Ambient Temperature

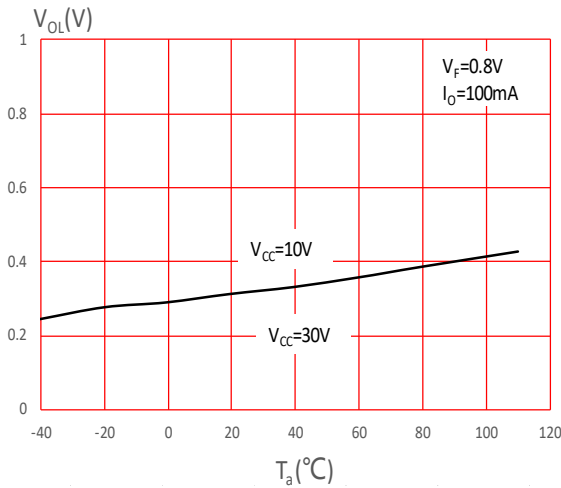


FIG.8: High-level Output Voltage vs. Ambient Temperature

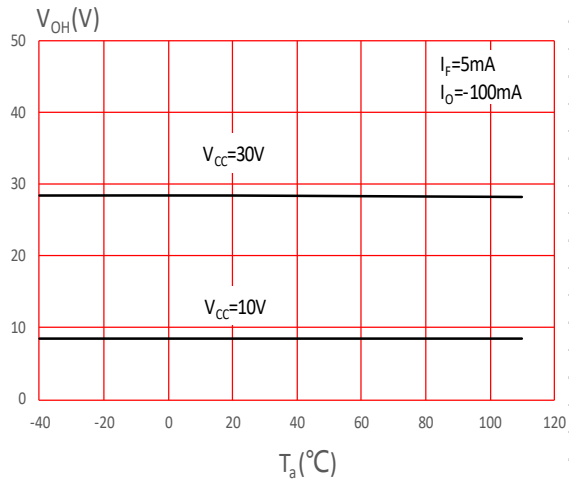


FIG.9: Low-level Output Voltage vs. Peak Low-level Output Current

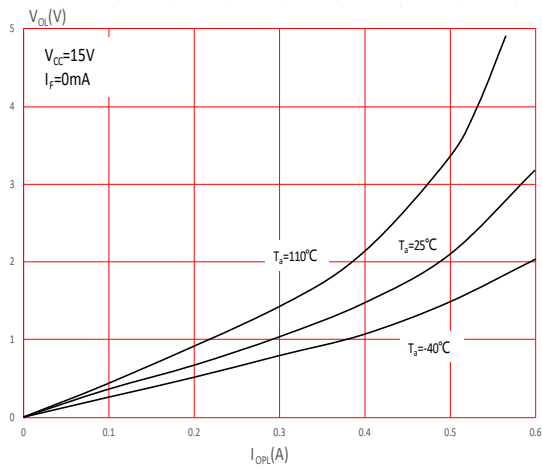


FIG.10: High-level Output Voltage Drop vs. Peak High-level Output Current

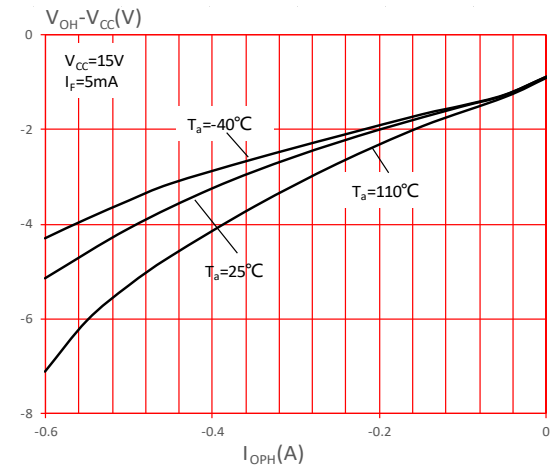


FIG.11: Propagation Delay Time, Pulse Width Distortion vs. Ambient Temperature

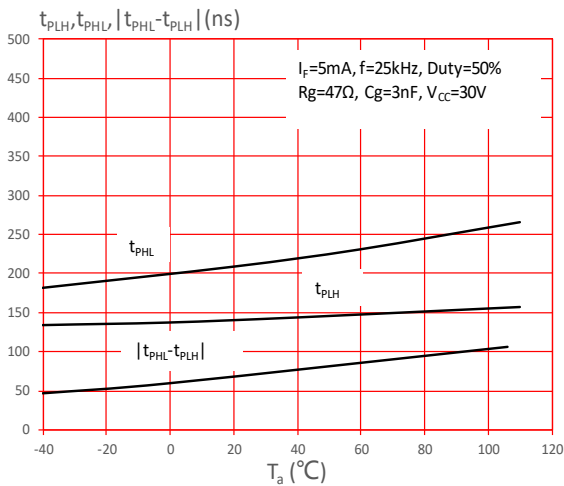


FIG.12: Propagation Delay Time, Pulse Width Distortion vs. Forward Current

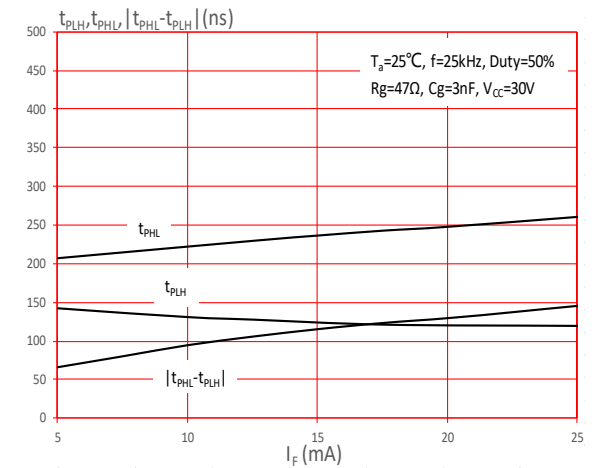
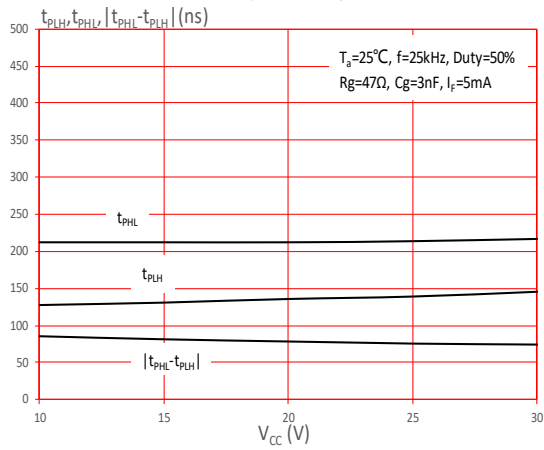


FIG.13: Propagation Delay Time,Pulse Width Distortion vs. Supply Voltage



Test Circuits

FIG.14: Switching Time Test Circuit and Waveform

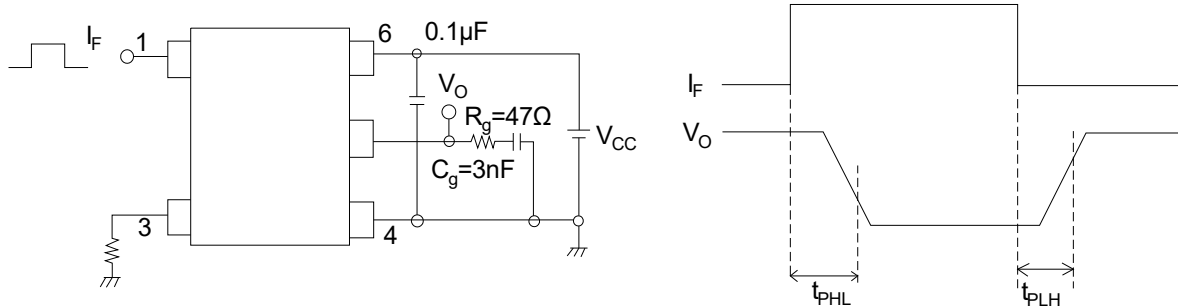
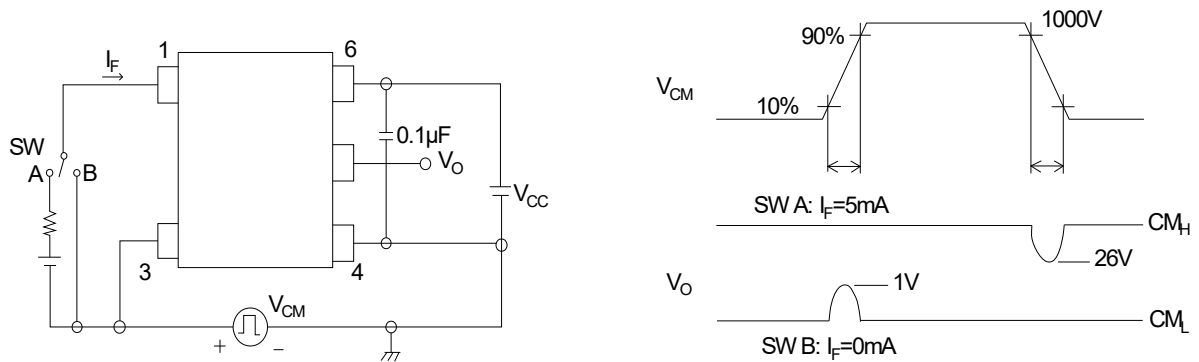
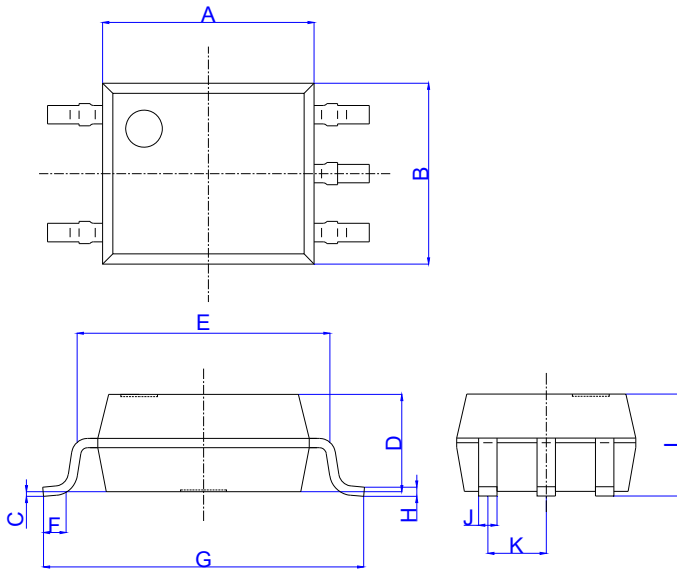


FIG.15: Common-Mode Transient Immunity Test Circuit and Waveform

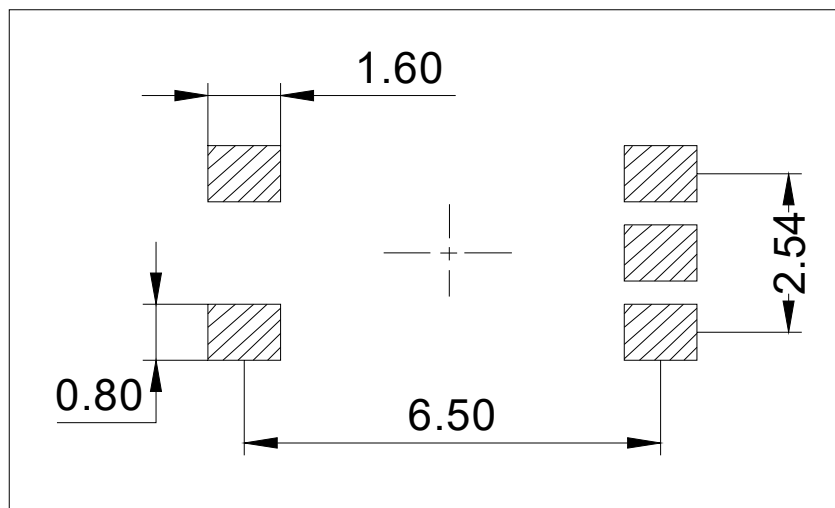


Package Dimension (Unit: mm)



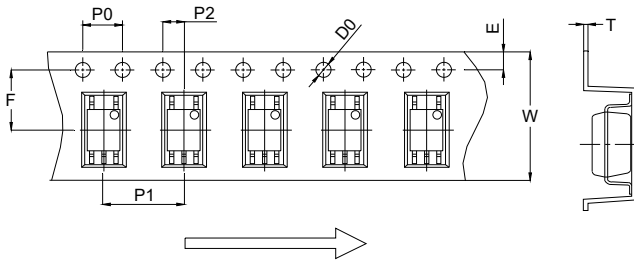
| Ref. | Dimensions | | | | | |
|------|-------------|------|------|--------|------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 4.40 | | 4.80 | 0.173 | | 0.189 |
| B | 3.60 | | 4.20 | 0.142 | | 0.165 |
| C | 0.00 | | 0.20 | 0.000 | | 0.008 |
| D | 1.90 | | 2.30 | 0.075 | | 0.091 |
| E | 5.00 | | 5.60 | 0.197 | | 0.220 |
| F | 0.34 | | 0.94 | 0.013 | | 0.037 |
| G | 6.70 | | 7.30 | 0.264 | | 0.287 |
| H | 0.10 | | 0.30 | 0.004 | | 0.012 |
| I | 2.00 | | 2.40 | 0.079 | | 0.094 |
| J | 0.25 | | 0.55 | 0.010 | | 0.022 |
| K | 1.02 | | 1.52 | 0.040 | | 0.060 |

RECOMMENDED SOLDER MASK (Dimensions in mm unless otherwise stated)



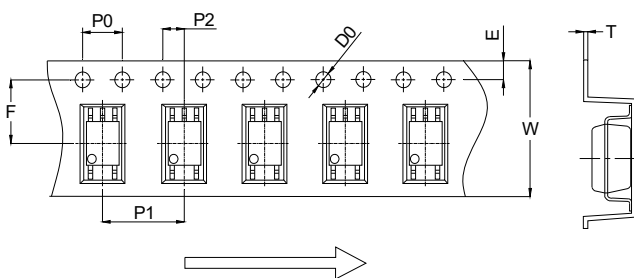
CARRIER TAPE SPECIFICATIONS (Dimensions in mm unless otherwise stated)

Option None



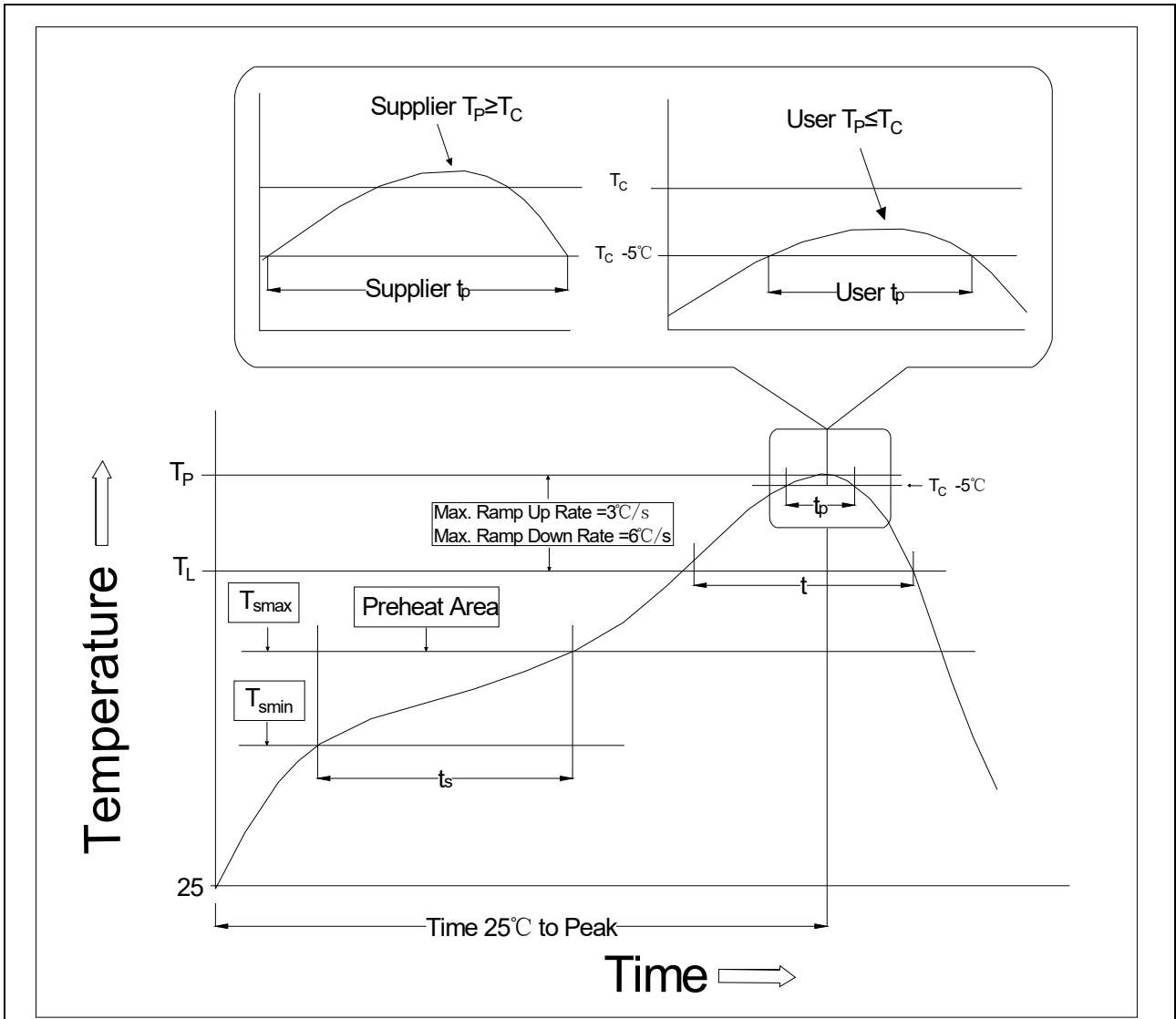
| Ref. | Dimensions | | | | | |
|------|-------------|-------|-------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| D0 | | 1.50 | 1.60 | | 0.059 | 0.063 |
| P0 | 3.90 | 4.00 | 4.10 | 0.154 | 0.157 | 0.161 |
| P1 | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 |
| P2 | 1.90 | 2.00 | 2.10 | 0.075 | 0.079 | 0.083 |
| E | 1.65 | 1.75 | 1.85 | 0.065 | 0.069 | 0.073 |
| F | 4.40 | 4.50 | 4.60 | 0.173 | 0.177 | 0.181 |
| T | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 |
| W | 11.90 | 12.00 | 12.30 | 0.469 | 0.472 | 0.484 |

Option R



| Ref. | Dimensions | | | | | |
|------|-------------|-------|-------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| D0 | | 1.50 | 1.60 | | 0.059 | 0.063 |
| P0 | 3.90 | 4.00 | 4.10 | 0.154 | 0.157 | 0.161 |
| P1 | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 |
| P2 | 1.90 | 2.00 | 2.10 | 0.075 | 0.079 | 0.083 |
| E | 1.65 | 1.75 | 1.85 | 0.065 | 0.069 | 0.073 |
| F | 4.40 | 4.50 | 4.60 | 0.173 | 0.177 | 0.181 |
| T | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 |
| W | 11.90 | 12.00 | 12.30 | 0.469 | 0.472 | 0.484 |

REFLOW INFORMATION




| Profile Feature | Sn-Pb Assembly Profile | Pb-Free Assembly Profile |
|---|------------------------|--------------------------|
| Temperature Min. (T _{smin}) | 100°C | 150°C |
| Temperature Max. (T _{smax}) | 150°C | 200°C |
| Time (t _s) from (T _{smin} to T _{smax}) | 60-120 seconds | 60-120 seconds |
| Ramp-up Rate (t _L to t _P) | 3°C/second max. | 3°C/second max. |
| Liquidus Temperature (T _L) | 183°C | 217°C |
| Time (t _L) Maintained Above (T _L) | 60-150 seconds | 60-150 seconds |
| Peak Body Package Temperature | 235°C+0°C/-5°C | 260°C+0°C/-5°C |
| Time (t _P) within 5°C of 260°C | 10 seconds | 10 seconds |
| Ramp-down Rate (T _P to T _L) | 3-6°C/second | 3-6°C/second |
| Time 25°C to Peak Temperature | 6 minutes max. | 8 minutes max. |

Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.
2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.
3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.
4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.
5. The component has a shelf life of one year when stored under standard conditions.
6. Recommend storage Temp.: 0~40°C;
Recommend storage humidity: <60%;
MSL level: MSL 1

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